

## Dual INT-A-PAK Low Profile “Half Bridge” (Standard Speed IGBT), 300 A



Dual INT-A-PAK Low Profile

### FEATURES

- Gen 4 IGBT technology
- Standard: optimized for hard switching speed
- Low  $V_{CE(on)}$
- Square RBSOA
- HEXFRED® antiparallel diode with ultrasoft reverse recovery characteristics
- Industry standard package
- $Al_2O_3$  DBC
- UL approved file E78996
- Designed for industrial level
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
COMPLIANT

PRIMARY CHARACTERISTICS	
$V_{CES}$	600 V
$I_C$ DC at $T_C = 25\text{ }^\circ\text{C}$	530 A
$V_{CE(on)}$ (typical) at 300 A, $25\text{ }^\circ\text{C}$	1.24 V
Speed	DC to 1 kHz
Package	Dual INT-A-PAK low profile
Circuit configuration	Half bridge

### BENEFITS

- Increased operating efficiency
- Performance optimized as output inverter stage for TIG welding machines
- Direct mounting on heatsink
- Very low junction to case thermal resistance

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	$V_{CES}$		600	V
Continuous collector current	$I_C$ <sup>(1)</sup>	$T_C = 25\text{ }^\circ\text{C}$	530	A
		$T_C = 80\text{ }^\circ\text{C}$	376	
Pulsed collector current	$I_{CM}$		800	
Clamped inductive load current	$I_{LM}$		800	
Diode continuous forward current	$I_F$	$T_C = 25\text{ }^\circ\text{C}$	219	
		$T_C = 80\text{ }^\circ\text{C}$	145	
Gate to emitter voltage	$V_{GE}$		$\pm 20$	V
Maximum power dissipation (IGBT)	$P_D$	$T_C = 25\text{ }^\circ\text{C}$	1136	W
		$T_C = 80\text{ }^\circ\text{C}$	636	
RMS isolation voltage	$V_{ISOL}$	Any terminal to case ( $V_{RMS}$ t = 1 s, $T_J = 25\text{ }^\circ\text{C}$ )	3500	V

#### Note

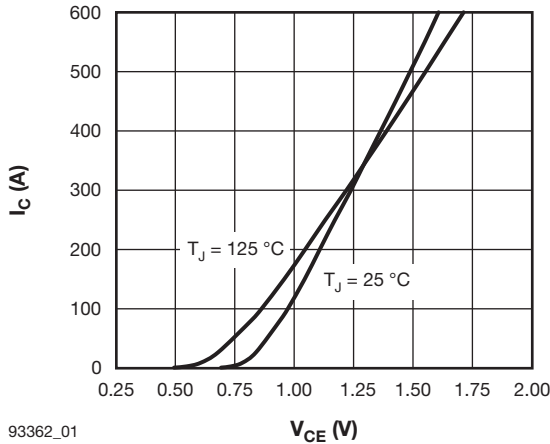
<sup>(1)</sup> Maximum continuous collector current must be limited to 500 A to do not exceed the maximum temperature of terminals



<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{BR(CES)}$	$V_{GE} = 0\text{ V}, I_C = 500\text{ }\mu\text{A}$	600	-	-	V
Collector to emitter voltage	$V_{CE(on)}$	$V_{GE} = 15\text{ V}, I_C = 150\text{ A}$	-	1.04	1.15	
		$V_{GE} = 15\text{ V}, I_C = 300\text{ A}$	-	1.24	1.45	
		$V_{GE} = 15\text{ V}, I_C = 150\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	0.96	1.06	
		$V_{GE} = 15\text{ V}, I_C = 300\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	1.22	1.42	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_C = 250\text{ }\mu\text{A}$	2.9	4.8	6.3	mA
Collector to emitter leakage current	$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}$ $V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	0.02 1.5	0.75 10	
Diode forward voltage drop	$V_{FM}$	$I_{FM} = 150\text{ A}$	-	1.23	1.39	V
		$I_{FM} = 300\text{ A}$	-	1.48	1.75	
		$I_{FM} = 150\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	1.17	1.33	
		$I_{FM} = 300\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	1.50	1.77	
Gate to emitter leakage current	$I_{GES}$	$V_{GE} = \pm 20\text{ V}$	-	-	$\pm 200$	nA

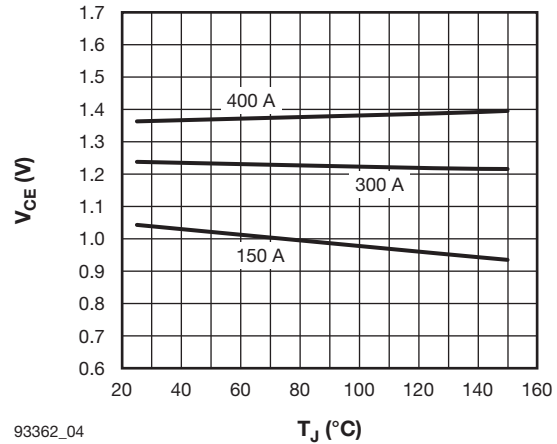
<b>SWITCHING CHARACTERISTICS</b> ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Turn-on switching loss	$E_{on}$	$I_C = 300\text{ A}, V_{CC} = 360\text{ V}, V_{GE} = 15\text{ V},$ $R_g = 1.5\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 25\text{ }^\circ\text{C}$	-	9	-	mJ
Turn-off switching loss	$E_{off}$		-	90	-	
Total switching loss	$E_{tot}$		-	99	-	
Turn-on switching loss	$E_{on}$	$I_C = 300\text{ A}, V_{CC} = 360\text{ V}, V_{GE} = 15\text{ V},$ $R_g = 1.5\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 125\text{ }^\circ\text{C}$	-	23	-	ns
Turn-off switching loss	$E_{off}$		-	133	-	
Total switching loss	$E_{tot}$		-	156	-	
Turn-on delay time	$t_{d(on)}$		-	442	-	
Rise time	$t_r$		-	301	-	
Turn-off delay time	$t_{d(off)}$		-	406	-	
Fall time	$t_f$	-	1570	-		
Reverse bias safe operating area	RBSOA	$T_J = 150\text{ }^\circ\text{C}, I_C = 800\text{ A}, V_{CC} = 400\text{ V}$ $V_P = 600\text{ V}, R_g = 22\text{ }\Omega, V_{GE} = 15\text{ V to } 0\text{ V},$ $L = 500\text{ }\mu\text{H}$	Fullsquare			
Diode reverse recovery time	$t_{rr}$	$I_F = 300\text{ A}, di_F/dt = 500\text{ A}/\mu\text{s},$ $V_{CC} = 400\text{ V}, T_J = 25\text{ }^\circ\text{C}$	-	150	179	ns
Diode peak reverse current	$I_{rr}$		-	43	59	A
Diode recovery charge	$Q_{rr}$		-	3.9	6.3	$\mu\text{C}$
Diode reverse recovery time	$t_{rr}$	$I_F = 300\text{ A}, di_F/dt = 500\text{ A}/\mu\text{s},$ $V_{CC} = 400\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	236	265	ns
Diode peak reverse current	$I_{rr}$		-	64	80	A
Diode recovery charge	$Q_{rr}$		-	8.6	11.1	$\mu\text{C}$

<b>THERMAL AND MECHANICAL SPECIFICATIONS</b>						
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	
Operating junction and storage temperature range	$T_J, T_{Stg}$	-40	-	150	$^\circ\text{C}$	
Junction to case per leg	IGBT	-	-	0.11	$^\circ\text{C}/\text{W}$	
	Diode	-	-	0.4		
Case to sink per module	$R_{thCS}$	-	0.05	-		
Mounting torque	case to heatsink: M6 screw	4	-	6	Nm	
	case to terminal 1, 2, 3: M5 screw	2	-	5		
Weight		-	270	-	g	



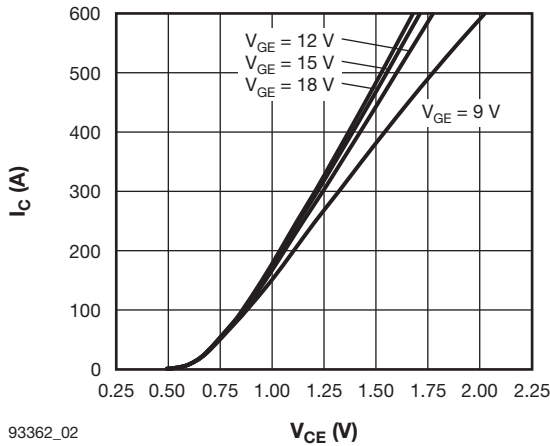
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Fig. 1 - Typical Output Characteristics,  
 $T_J = 25\text{ }^\circ\text{C}$ ,  $V_{GE} = 15\text{ V}$



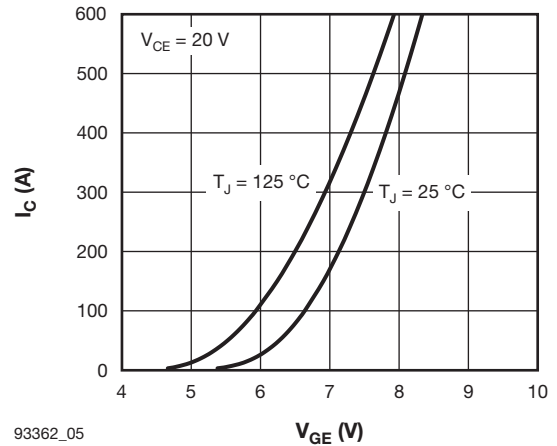
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Fig. 4 - Typical IGBT Collector to Emitter Voltage vs.  
Junction Temperature,  
 $V_{GE} = 15\text{ V}$



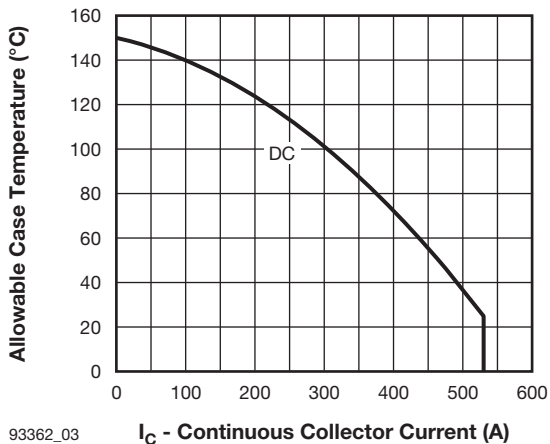
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Fig. 2 - Typical Output Characteristics,  
 $T_J = 125\text{ }^\circ\text{C}$



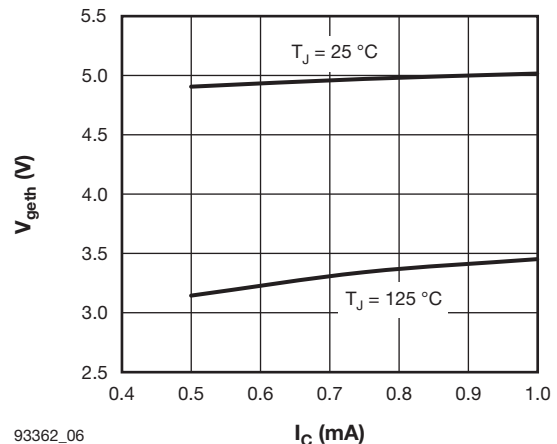
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Fig. 5 - Typical IGBT Transfer Characteristics



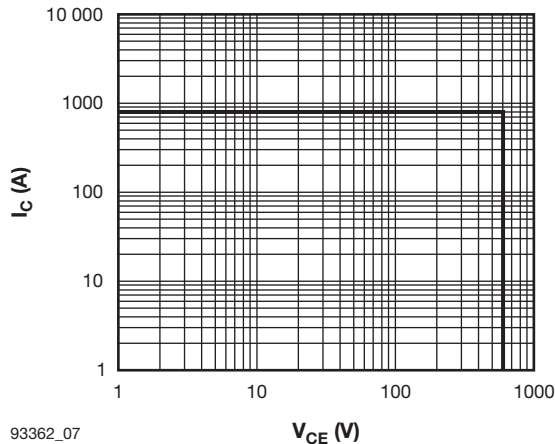
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Fig. 3 - Maximum DC IGBT Collector Current vs.  
Case Temperature



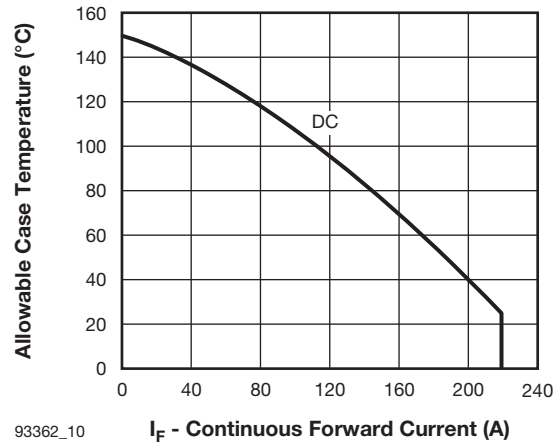
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Fig. 6 - Typical IGBT Gate Threshold Voltage



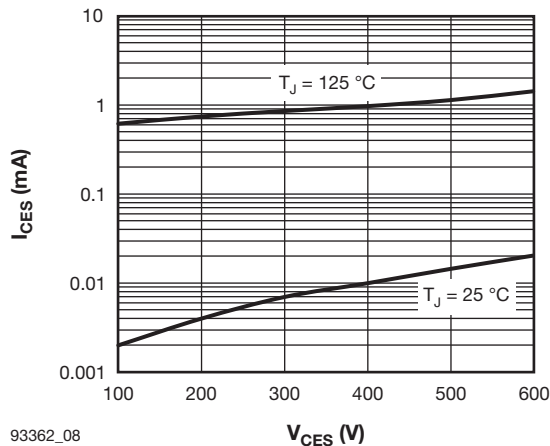
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Fig. 7 - IGBT Reverse Bias SOA,  
 $T_J = 150\text{ }^\circ\text{C}$ ,  $V_{GE} = 15\text{ V}$ ,  $R_g = 22\ \Omega$



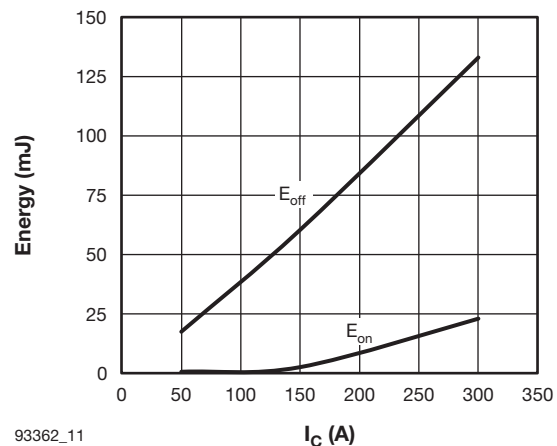
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Fig. 10 - Maximum DC Forward Current vs. Case Temperature



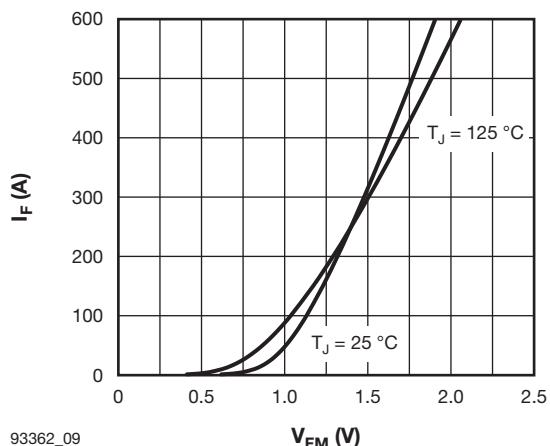
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Fig. 8 - Typical IGBT Zero Gate Voltage Collector Current



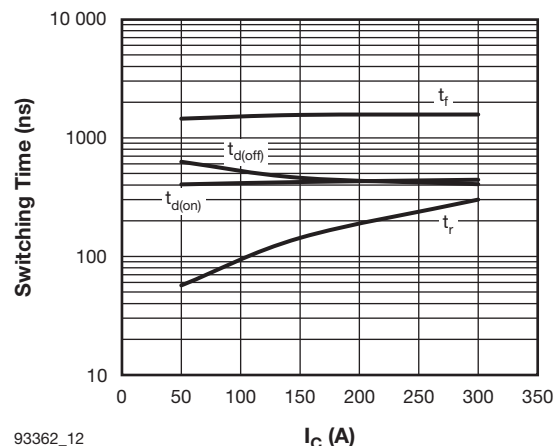
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Fig. 11 - Typical IGBT Energy Loss vs.  $I_C$ ,  
 $T_J = 125\text{ }^\circ\text{C}$ ,  $V_{CC} = 360\text{ V}$ ,  $R_g = 1.5\ \Omega$ ,  
 $V_{GE} = 15\text{ V}$ ,  $L = 500\ \mu\text{H}$



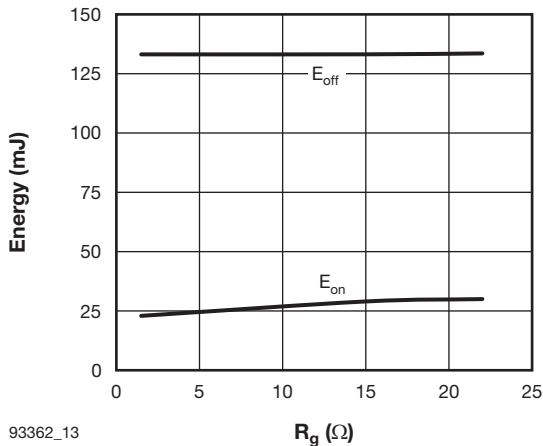
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Fig. 9 - Typical Diode Forward Characteristics



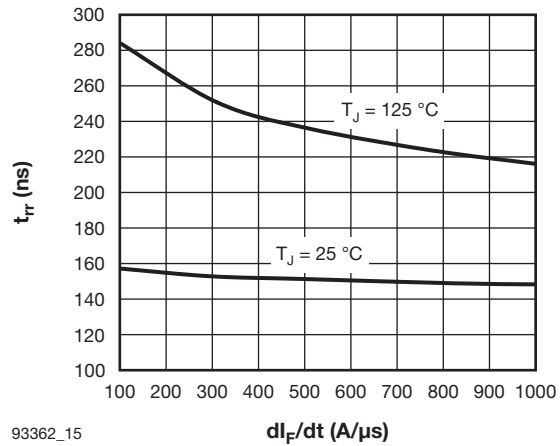
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Fig. 12 - Typical IGBT Switching Time vs.  $I_C$ ,  
 $T_J = 125\text{ }^\circ\text{C}$ ,  $V_{CC} = 360\text{ V}$ ,  $R_g = 1.5\ \Omega$ ,  
 $V_{GE} = 15\text{ V}$ ,  $L = 500\ \mu\text{H}$



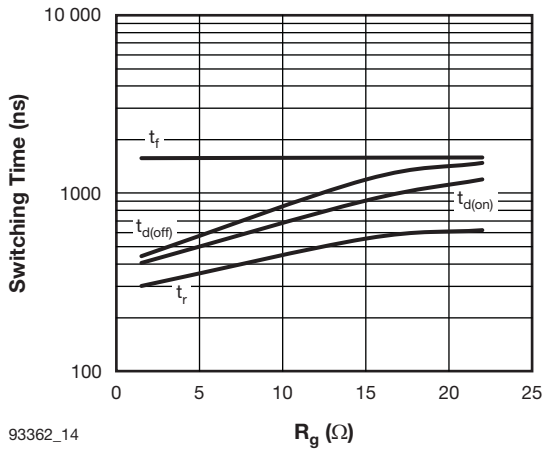
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Fig. 13 - Typical IGBT Energy Loss vs.  $R_g$ ,  
 $T_J = 125\text{ }^\circ\text{C}$ ,  $I_C = 300\text{ A}$ ,  $V_{CC} = 360\text{ V}$ ,  
 $V_{GE} = 15\text{ V}$ ,  $L = 500\text{ }\mu\text{H}$



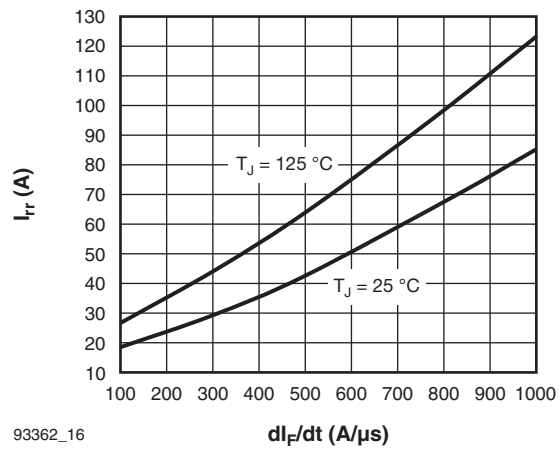
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Fig. 15 - Typical Reverse Recovery Time vs.  $dl_F/dt$ ,  
 $V_{CC} = 400\text{ V}$ ,  $I_F = 300\text{ A}$



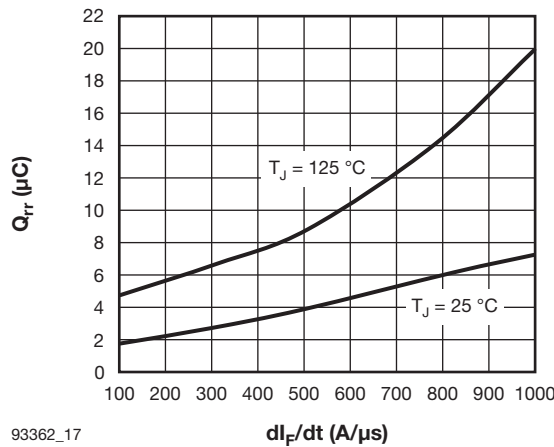
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Fig. 14 - Typical IGBT Switching Time vs.  $R_g$ ,  
 $T_J = 125\text{ }^\circ\text{C}$ ,  $I_C = 300\text{ A}$ ,  $V_{CC} = 360\text{ V}$ ,  
 $V_{GE} = 15\text{ V}$ ,  $L = 500\text{ }\mu\text{H}$



93362\_16

Fig. 16 - Typical Reverse Recovery Current vs.  $dl_F/dt$ ,  
 $V_{CC} = 400\text{ V}$ ,  $I_F = 300\text{ A}$



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Fig. 17 - Typical Reverse Recovery Charge vs.  $dl_F/dt$ ,  
 $V_{CC} = 400\text{ V}$ ,  $I_F = 300\text{ A}$

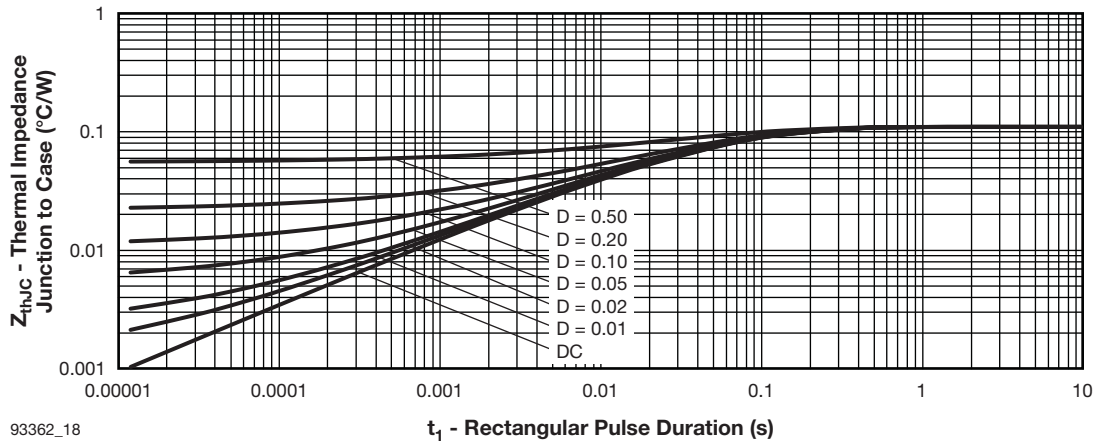


Fig. 18 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics (IGBT)

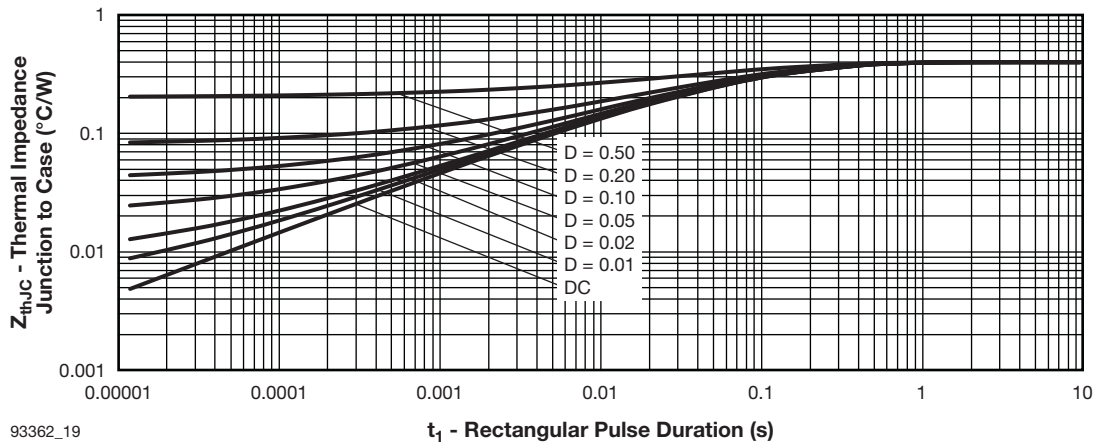


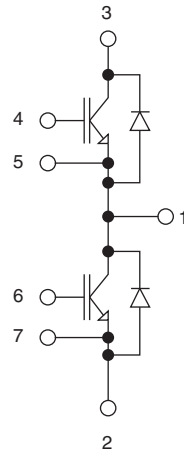
Fig. 19 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics (Diode)

**ORDERING INFORMATION TABLE**

Device code	<b>G</b>	<b>A</b>	<b>300</b>	<b>T</b>	<b>D</b>	<b>60</b>	<b>S</b>
	①	②	③	④	⑤	⑥	⑦
	<b>1</b>	-	Insulated gate bipolar transistor (IGBT)				
	<b>2</b>	-	A = Gen 4 IGBT				
	<b>3</b>	-	Current rating (300 = 300 A)				
	<b>4</b>	-	Circuit configuration (T = half bridge)				
	<b>5</b>	-	Package indicator (D = dual INT-A-PAK low profile)				
	<b>6</b>	-	Voltage rating (60 = 600 V)				
	<b>7</b>	-	Speed / type (S = standard speed IGBT)				



**CIRCUIT CONFIGURATION**



LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95435">www.vishay.com/doc?95435</a>



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